

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

Claim 1. (Currently Amended) A semiconductor device, comprising:

- a SOI wafer having a stacked structure of a first silicon layer, a buried insulating film and a second silicon layer;
- ~~a trench formed by removing a predetermined region of the second silicon layer;~~
- ~~a first silicide layer formed at side walls of the trench;~~
- a device isolation film defining disposed in the second silicon layer, wherein the device isolation film defines an active region of the SOI wafer ~~formed by filling the trench;~~
- a gate electrode having a gate insulation film ~~formed~~ disposed on the active region of the SOI wafer;
- an insulation spacer ~~formed~~ disposed at side walls of the gate electrode;
- impurity junction regions ~~formed~~ disposed at both sides of the gate electrode in the active region of the SOI wafer;
- a first silicide layer disposed at an interface of the impurity junction region and the device isolation film; and
- a second silicide layer formed on the gate electrode and the impurity junction region.

Claim 2. (Original): The semiconductor device according to claim 1, wherein the first and the second silicide layers comprise a metal selected from the group consisting of titanium, cobalt, nickel, and tungsten.

Claims 3–9. (Canceled)